

# **SWITCHMODE SERIES NPN POWER TRANSISTORS**

... designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220 V switchmode applications such as switching regulator's,inverters,DC -DC conveter, Motor controls, Solenoiid / Relay drivers and Deflection circuits.

#### **FEATURES**:

\*Collector-Emitter Sustaining Voltage-

V<sub>CEO(SUS)</sub> = 400 V and 300 V \* Collector-Emitter Saturation Voltage -

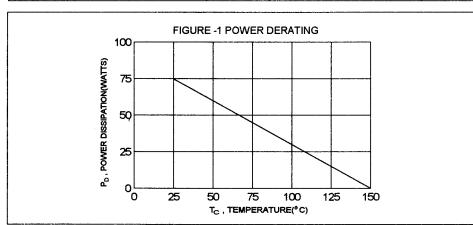
 $V_{CE(sat)} = 1.0 \text{ V (Max.)} \bigcirc I_{C} = 4.0 \text{ A}, I_{B} = 1.0 \text{ A}$ \* Switching Time -  $t_{i}$  =0.9 us (Max.)  $\bigcirc I_{C} = 2.0 \text{ A}$ 

# **MAXIMUM RATINGS**

Characteristic	Symbol	MJE13004	MJE13005	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	300	400	V
Collector-Emitter Voltage	V <sub>CEV</sub>	600	700	V
Emitter-Base Voltage	V <sub>EBO</sub>	9	0.0	٧
Collector Current - Continuous - Peak	I <sub>C</sub>	· -	.0 .0	Α
Base current	l <sub>B</sub>	2	.0	Α
Total Power Dissipation @T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	75 0.6		W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-65 to	+150	°C

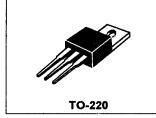
# THERMAL CHARACTERISTICS

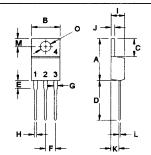
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	Rθjc	1.67	°C/W



# NPN MJE13004 MJE13005

**4 AMPERE POWER TRANASISTORS** 300-400 VOLTS 75 WATTS





PIN 1.BASE 2.COLLECTOR
3.EMITTER
4.COLLECTOR(CASE)

D04	MILLIMETERS			
DIM	MIN	MAX		
A B C D E F G	14.68 9.78 5.01 13.06 3.57 2.42 1.12	15.31 10.42 6.52 14.62 4.07 3.66 1.36		
H-JK- <b>M</b> 0	0.72 4.22 1.14 2.20 0.33 2.48 3.70	0.96 4.98 1.38 2.97 0.55 2.98 3.90		

Cha	racteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0)	Voltage MJE13004 MJE13005	V <sub>CEO(sus)</sub>	300 400		V
Collector Cutoff Current (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> =1.5 V) (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> =1.5 V, T <sub>C</sub> =100 °C)		I <sub>CEV</sub>		1.0 5.0	mA
Emitter Cutoff Current (V <sub>EB</sub> = 9.0 V, I <sub>C</sub> = 0)		I <sub>EBO</sub>		1.0	mA
ON CHARACTERISTICS (	1)				
DC Current Gain ( I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 5.0 V ) ( I <sub>C</sub> = 2.0 A, V <sub>CE</sub> = 5.0 V )		hFE	10 8.0	60 40	
Collector-Emitter Saturation ( $I_c$ = 1.0 A, $I_B$ = 200 mA) ( $I_c$ = 2.0 A, $I_B$ = 500 mA) ( $I_c$ = 4.0 A, $I_B$ = 1.0 A)	Voltage	V <sub>CE(sat)</sub>		0.5 0.6 1.0	V
Base-Emitter Saturation Volta ( $I_c$ = 1.0 A, $I_B$ = 200 mA) ( $I_C$ = 2.0 A, $I_B$ = 500 mA)	age	V <sub>BE(sat)</sub>		1.2 1.6	V
DYNAMIC CHARACTERIS	STICS				
Current Gain - Bandwidth Product (I <sub>C</sub> = 500 mA , V <sub>CE</sub> = 10 V ,f = 1.0 MHz )		f <sub>T</sub>	4.0		MHz
SWITCHING CHARACTER	RISTICS				
Delay Time	V <sub>CC</sub> = 125 V, I <sub>C</sub> = 2.0 A	t <sub>d</sub>		0.1	us
Rise Time	I <sub>B1</sub> = -I <sub>B2</sub> =0.4A,	t <sub>r</sub>		0.7	us

t s

t,

4.0

0.9

us

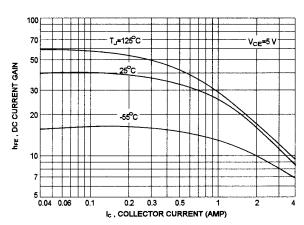
us

# Fall Time (1) Pulse Test: Pulse Width =300 us,Duty Cycle ≤ 2.0%

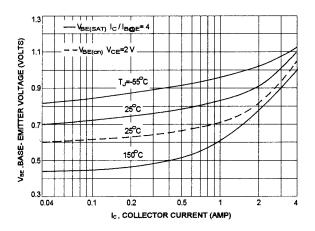
tp = 25 us,Duty Cycle ≦1.0%

Storage Time

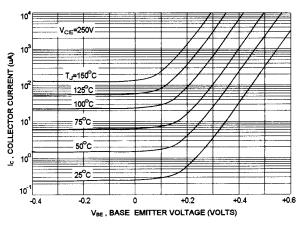
#### DC CURRENT GAIN



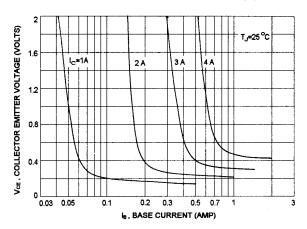
# BASE-EMITTER VOLTAGE



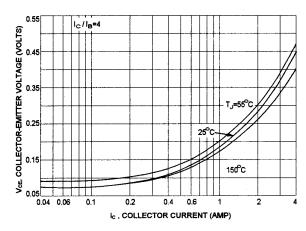
# **COLLECTOR CUT-OFF REGION**



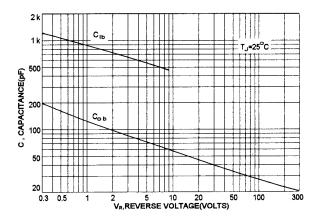
#### **COLLECTOR SATURATION REGION**

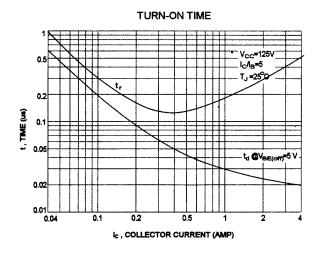


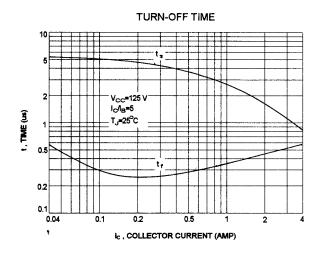
#### COLLECTOR-EMITTER SATURATION VOLTAGE



#### CAPACITANCE







#### **ACTIVE REGION SAFE OPERATING AREA**

